

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBSS4160QA.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V
I _C	collector current			-	-	-1	А
I _{CM}	peak collector current	$t_p \le 1 ms; pulsed$		-	-	-1.5	А
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	225	330	mΩ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	Е	emitter		в-
3	С	collector	4 3	۱۳۳ ۲
4	С	collector	Transparent top view	sym132
			DFN1010D-3 (SOT1215)	

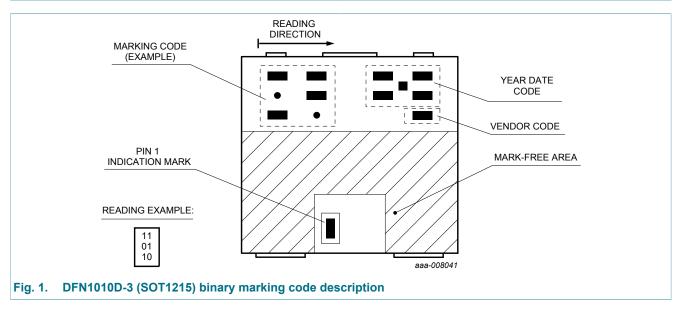
6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS5160QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5160QA	10 10 10



PBSS5160QA

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-1	А
I _{CM}	peak collector current	$t_p \le 1 ms$; pulsed		-	-1.5	А
I _B	base current			-	-0.3	А
I _{BM}	peak base current	$t_p \le 1 ms; pulsed$		-	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

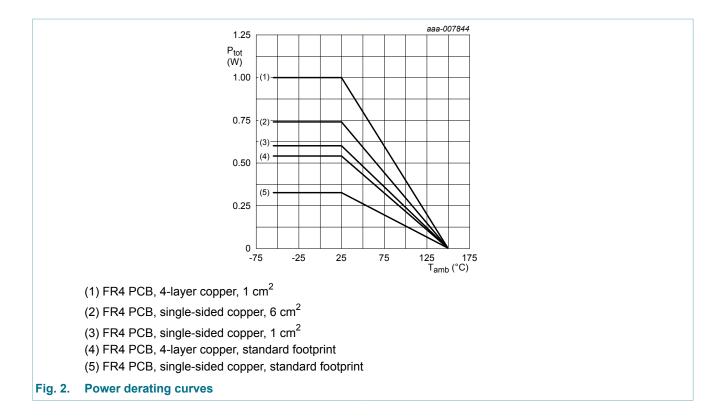
^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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9. Thermal characteristics

Table 6. T	Table 6. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	385	K/W
	from junction to ambient		[2]	-	-	209	K/W
			[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			[5]	-	-	125	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

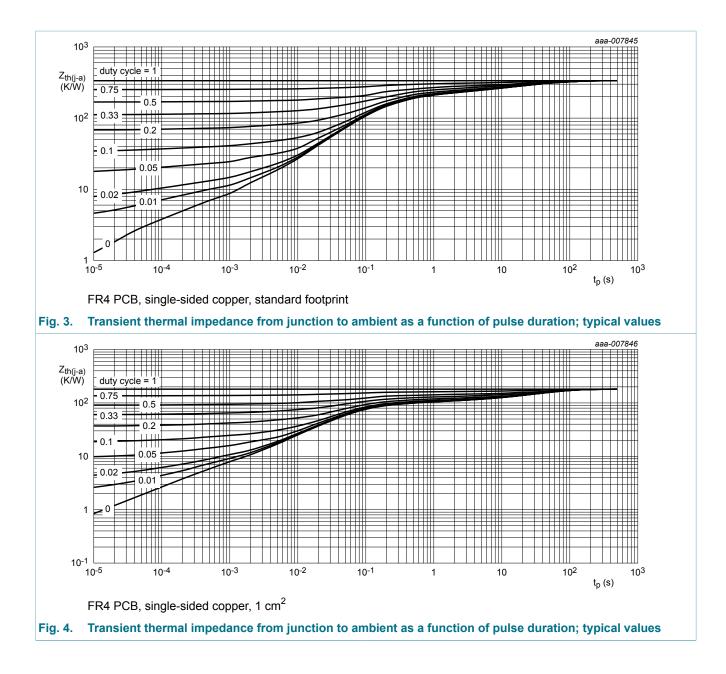
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

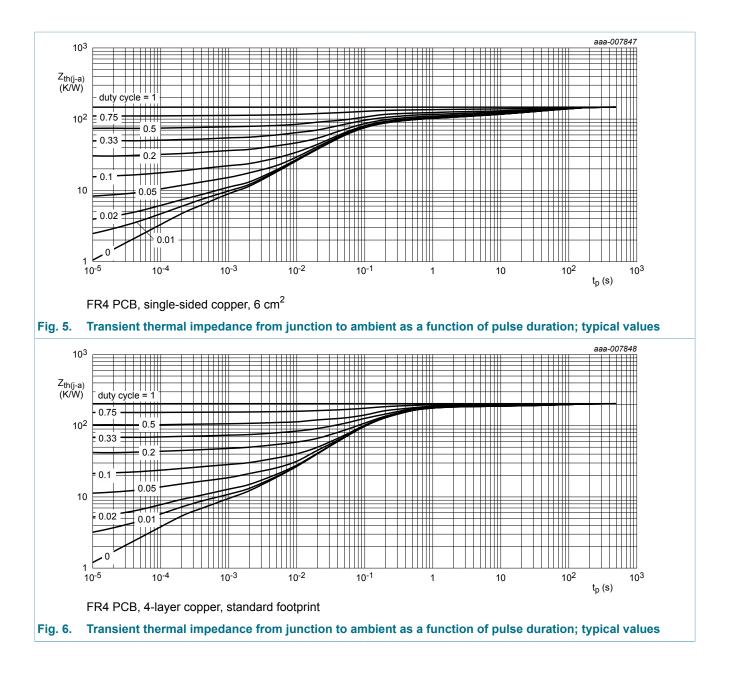


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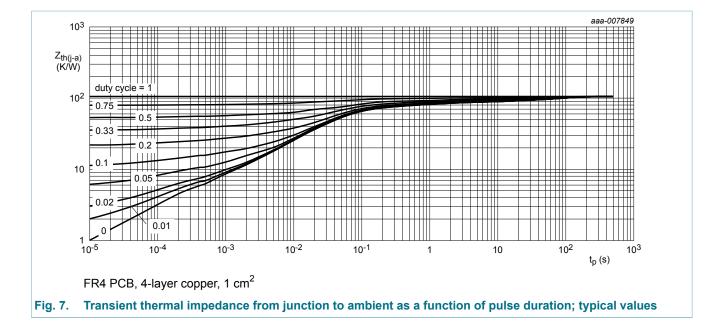
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10. Characteristics

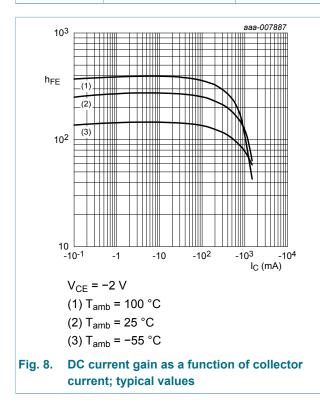
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -48 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE} DC current gain	$V_{CE} = -2 \text{ V; } I_C = -100 \text{ mA; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C; } \text{pulsed}$	160	250	-		
		$\label{eq:VCE} \begin{array}{l} V_{CE} \texttt{=} \texttt{-2} \; V \texttt{;} \; I_{C} \texttt{=} \texttt{-500 mA}\texttt{;} \; t_{p} \texttt{\leq} \texttt{300 } \mu \texttt{s}\texttt{;} \\ \\ \bar{D} \texttt{\leq} \texttt{0.02} \; \texttt{;} \; T_{amb} \texttt{=} \texttt{25} \; \texttt{^{\circ}C}\texttt{;} \; \texttt{pulsed} \end{array}$	120	185	-	
		$\begin{split} V_{CE} &= -2 \text{ V}; \text{I}_{C} = -1 \text{ A}; \text{t}_{p} \leq 300 \mu\text{s}; \\ \delta &\leq 0.02 ; \text{T}_{amb} = 25 ^\circ\text{C}; \text{pulsed} \end{split}$	85	125	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -500 \text{ mA}; I_{B} = -50 \text{ mA}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C}$	-	-125	-190	mV
		$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C}$	-	-315	-460	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-225	-330	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$; T_{amb} = 25 °C	-	225	330	mΩ

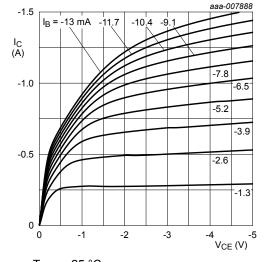
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat} base-emitter saturation voltage	base-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-0.88	-1	V
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-0.94	-1.05	V
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-0.97	-1.1	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -0.5 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-0.8	-0.9	V
t _d	delay time	V_{CC} = -10 V; I _C = -0.5 A; I _{Bon} = -25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = 25 mA; T _{amb} = 25 °C	-	35	-	ns
t _{on}	turn-on time	-	-	50	-	ns
t _s	storage time		 -	300	-	ns
t _f	fall time		-	50	-	ns
t _{off}	turn-off time		-	350	-	ns
f _T	transition frequency	V_{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	100	150	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	12	15	pF



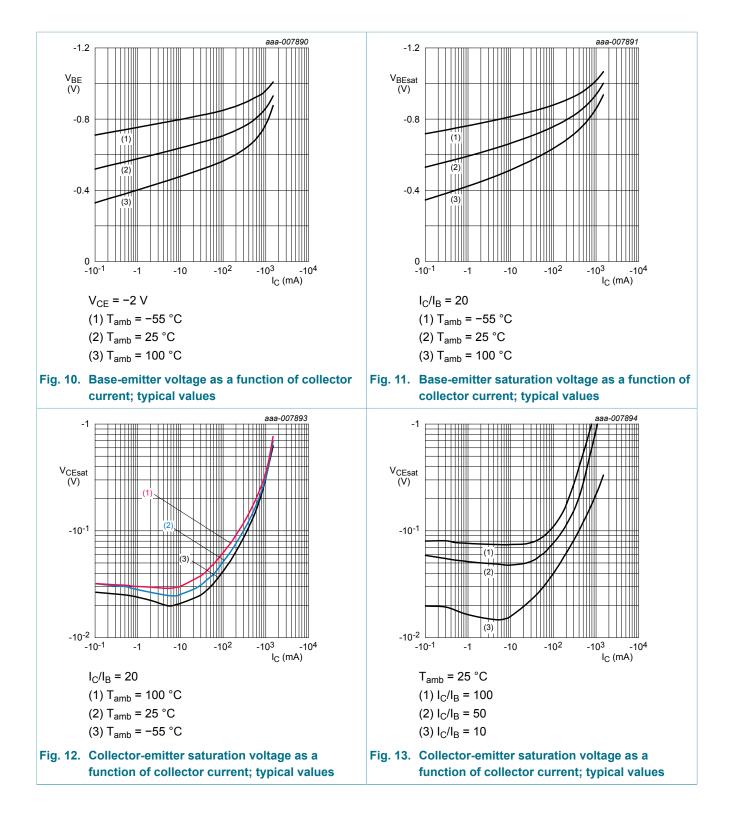


T_{amb} = 25 °C

Fig. 9. Collector current as a function of collectoremitter voltage; typical values

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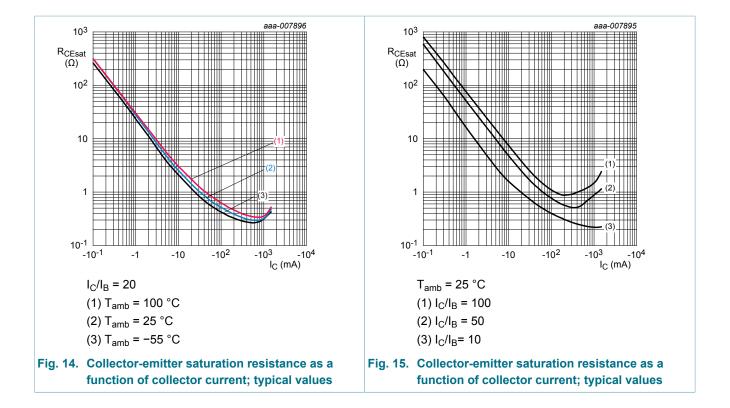
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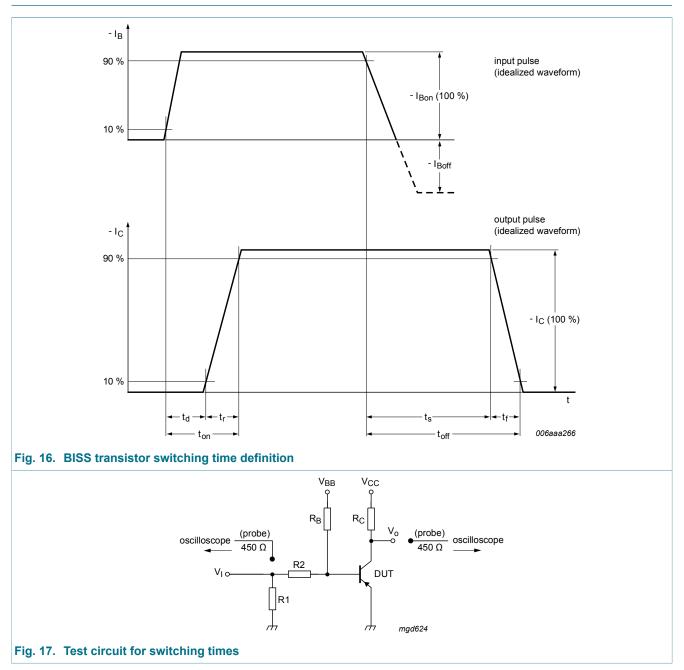
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11. Test information

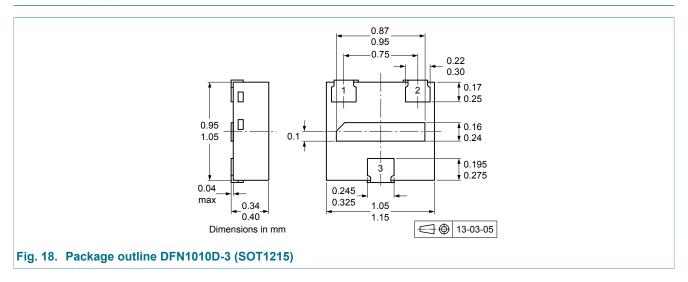


This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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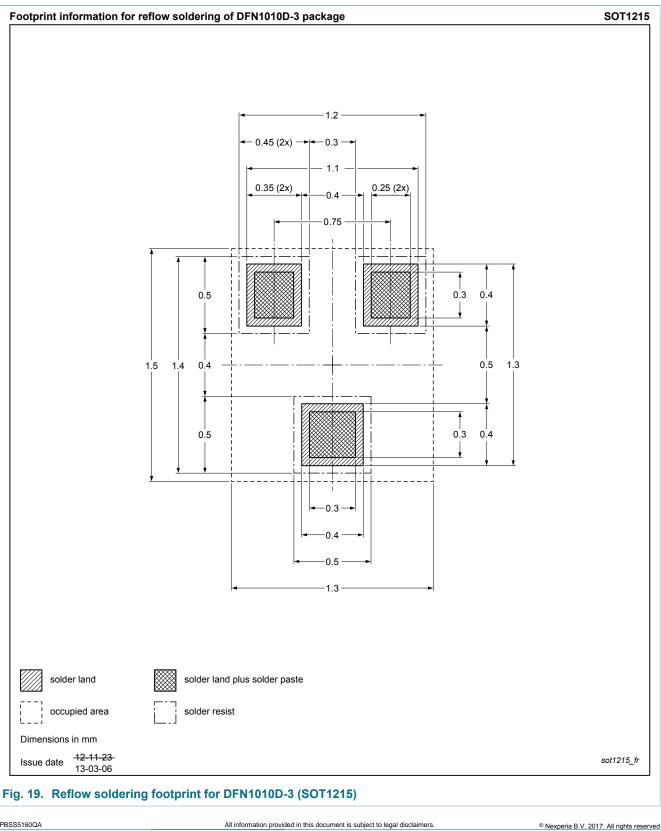
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history				
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5160QA v.1	20130823	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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